

L Number	Hits	Search Text	DB	Time stamp
-	5	"837265"	USPAT; US-PGPUB	2002/03/25 16:45
-	588	((427/457,487,492,508,509,516,532,553,554,555 and sinter\$5	USPAT;557,562000403025596;596,58,96)	
-	0	((((427/457,487,492,508,509,516,532,553,554,555 and sinter\$5) and laser with puls\$6) and	USPAT;557,8602563/28115950596,58,9	
-	3606	aerogel	USPAT; US-PGPUB	2002/03/25 16:50
-	86	((((427/457,487,492,508,509,516,532,553,554,555 and sinter\$5) and laser with puls\$6	USPAT;557,58002603888,5950596,58,96)	
-	129	laser with puls\$6 same sinter\$6	USPAT; US-PGPUB	2002/03/28 15:05
-	6	((laser with puls\$6 same sinter\$6) and heat\$5 with (substrate or base)) and	USPAT; US-PGPUB	2002/03/28 15:17
-	7	damag\$6 with substrate	USPAT; US-PGPUB	
-	1	((laser with puls\$6 same sinter\$6) and damag\$6 with substrate) not (((laser with puls\$6 same sinter\$6) and heat\$5 with (substrate or base)) and damag\$6 with	USPAT; US-PGPUB	2002/03/28 15:22
-	60	substrate)	USPAT; US-PGPUB	2002/04/01 11:27
-	6	(laser with puls\$6 same sinter\$6) and heat\$5 with (substrate or base)	USPAT; US-PGPUB	2002/04/01 11:27
-	5375	((427/457,487,492,508,509,516,532,553,554,555 and anneal\$67	USPAT;557,5612002/08105951596;58,96)	
-	623	((427/457,487,492,508,509,516,532,553,554,555 and anneal\$6	USPAT;557,562000403001596;596,58,96)	
-	623	((427/457,487,492,508,509,516,532,553,554,555 and anneal\$6	USPAT;557,562000403001596;596,58,96)	
-	186	((((427/457,487,492,508,509,516,532,553,554,555 and anneal\$6) and puls\$6 with laser	USPAT;557,58002604581,5953896,58,96)	
-	94	and anneal\$6) and puls\$6 with laser) not	US-PGPUB	2002/04/08115938596,58,9
-	61	((target ablat\$6) and puls\$6 with laser) not	USPAT;556,5572002/06405811596;596,58,	
-		(target ablat\$6) and (heat\$5 with	US-PGPUB	
-	18	(\$#0\$#t#2#4B#s#87,492,508,509,516,532,553,554,555 and anneal\$6) and puls\$6 with laser) not	USPAT;556,552000103001581;595,596,58	
-	22	(target ablat\$6) and (heat\$5 with	US-PGPUB	
-	62	(\$#0\$#t#2#4B#s#87)48#d5#0#h#5#0#s#816,532,553,554,555 and anneal\$6 same puls\$6 with laser	USPAT;557,562000403001596;596,58,96)	
-	34	and anneal\$6 same puls\$6 with laser) not	US-PGPUB	58002604581,595596,58,96
-	35	((target ablat\$6) and (heat\$5 with	USPAT;557,58002604581,595596,58,96)	
-	9	(\$#0\$#t#2#4B#s#87)5#0#d5#0#h#5#0#s#8,532,553,554,555 and anneal\$6 same puls\$6 with laser) and	US-PGPUB	2002/04/08115957596,58,9
-	2282	(heat\$5 same puls\$6 with laser) and	USPAT; US-PGPUB	2002/04/01 12:29
-	0	sinter\$6 same heat\$3 with substrateb same	USPAT; US-PGPUB	2002/04/01 12:30
-	17	puls\$6 with laser	USPAT; US-PGPUB	2002/04/01 12:57
-	341	sinter\$6 same heat\$3 with substrate same	USPAT; US-PGPUB	2002/04/01 13:06
-	3	puls\$6 with laser	USPAT; US-PGPUB	2002/04/01 13:03
-	17	adhe\$8 same sinter\$6 same heat\$6 with	USPAT; US-PGPUB	2002/04/01 13:06
-	34	substrate	USPAT; US-PGPUB	2002/04/01 13:12
-		(adhe\$8 same sinter\$6 same heat\$6 with	USPAT; US-PGPUB	
-		substrate) same SEMICONDUCTOR	USPAT; US-PGPUB	

-	11102	sinter\$3.ab.	USPAT; US-PGPUB	2002/04/01 13:13
-	198	sinter\$3.ab. same heat\$3 with substrate	USPAT; US-PGPUB	2002/04/01 13:19
-	3	sinter\$3.ab. same heat\$3 with substrate same laser	USPAT; US-PGPUB	2002/04/01 13:14
-	38	sintering.ab. same heating with substrate	USPAT; US-PGPUB	2002/04/01 13:18
-	5	sintering.ab. same heating with substrate same semiconductor	USPAT; US-PGPUB	2002/04/01 13:18
-	40	sinter\$3.ab. same heat\$3 with substrate same semiconductor	USPAT; US-PGPUB	2002/04/01 13:19
-	1	("5223453").PN.	USPAT; US-PGPUB	2002/04/01 14:33
-	11	sinter\$3.ab. same thermal with barrier	USPAT; US-PGPUB	2002/04/01 15:06
-	501	aerogel and (sinter\$3 or anneal\$3)	USPAT; US-PGPUB	2002/04/01 14:49
-	77	aerogel same (sinter\$3 or anneal\$3)	USPAT; US-PGPUB	2002/04/01 14:47
-	26	aerogel and (sinter\$3 or anneal\$3).ab.	USPAT; US-PGPUB	2002/04/01 14:47
-	364	aerogel and (sinter\$3)	USPAT; US-PGPUB	2002/04/01 14:49
-	18	aerogel and (sinter\$3).ab.	USPAT; US-PGPUB	2002/04/01 14:49
-	970	((505/500) or (419/1,10,21)).CCLS.	USPAT; US-PGPUB	2002/04/01 15:06
-	477	((505/500) or (419/1,10,21)).CCLS.) and sintering	USPAT; US-PGPUB	2002/04/01 15:06
-	2	((505/500) or (419/1,10,21)).CCLS.) and sintering) and thermal with barrier	USPAT; US-PGPUB	2002/04/01 15:07
-	3	((505/500) or (419/1,10,21)).CCLS.) and sintering) and (thermal protective) with barrier	USPAT; US-PGPUB	2002/04/01 15:07
-	83	sintering same (thermal protective) with barrier	USPAT; US-PGPUB	2002/04/01 15:07
-	38	sintering with (thermal protective) with barrier	USPAT; US-PGPUB	2002/04/01 15:45
-	508	sintering with (thermal protective) with layer	USPAT; US-PGPUB	2002/04/01 15:45
-	376	sintering with (thermal) with layer	USPAT; US-PGPUB	2002/04/01 15:46
-	15	sintering.ab. with (thermal) with layer	USPAT; US-PGPUB	2002/04/01 16:11
-	3	sintering.ab. same (thermal) near2 layer	USPAT; US-PGPUB	2002/04/01 16:12
-	13	sintering.ab. same shield	USPAT; US-PGPUB	2002/04/01 16:16
-	0	sintering same aerogel same semiconductor same layer	USPAT; US-PGPUB	2002/04/01 16:17
-	1	sintering same aerogel same semiconductor	USPAT; US-PGPUB	2002/04/01 16:17
-	2	sinter\$3 same aerogel same semiconductor	USPAT; US-PGPUB	2002/04/01 16:17
-	40471	pyrometer same sintering	USPAT; US-PGPUB	2002/04/01 16:47
-	47	pyrometer same sintering	USPAT; US-PGPUB	2002/04/01 16:49
-	0	pyrometer same sintering and spot adj Size	USPAT; US-PGPUB	2002/04/01 16:49
-	2	pyrometer same sintering and spot	USPAT; US-PGPUB	2002/04/01 16:50
-	59	pyrometer with spot	USPAT; US-PGPUB	2002/04/01 16:52